# Weyl semimetals: the next (next) graphene?

#### Leon Balents, KITP, UCSB



Anton Burkov, U. Waterloo



Gabor Halasz, U. Cambridge

#### Outline

- Weyl fermions
- Where to find them
- TR-breaking and Hall effects
- I-breaking
- Graphene-like physics

# Weyl Fermion

• Massless Dirac fermion with fixed handedness



 described by a 2-component spinor unlike 4-component (spin+particle/hole) Dirac spinor

$$H = v\vec{\sigma} \cdot \vec{k}$$

### Level repulsion

- von Neumann and Wigner, 1929
  - In QMs, 3 parameters must be tuned to make 2 levels cross
  - led to a whole field of statistics of energy levels, quantum chaos,...



# Weyl points in band theory

- In 3d band structures with non-degenerate bands - *lacking either inversion or TR* - this happens at isolated points
  - the non-degeracy of course requires breaking spin-rotation symmetry typically by SOC

PHYSICAL REVIEW

937

Accidental Degeneracy in the Energy Bands of Crystals

CONYERS HERRING Princeton University, Princeton, New Jersey (Received June 16, 1937) For a crystal without an inversion center, the energy separation  $\delta E(\mathbf{k} + \mathbf{\kappa})$  in the neigborhood of a point  $\mathbf{k}$  where contact of equivalent manifolds occurs may be expected to be of the order of  $\kappa$  as  $\kappa \rightarrow 0$ , for all directions of  $\kappa$ .

# Ln<sub>2</sub>Ir<sub>2</sub>O<sub>7</sub> Pyrochlores





• Series of materials shows systematic MITs

• Ir<sup>4+</sup> has  $\lambda \approx 0.5 \text{eV}$ 

D. Yanagashima, Y. Maeno, 2001



K. Matsuhira et al, 2011

#### **Exotic Possibilities**

• Topological Mott Insulator?



#### D. Pesin+LB, 2010

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Probably not: commensurate magnetic order seen in µSR

S. Zhao et al, 2011

#### Weyl semimetal? X.Wan et al, 2011

#### • LDA+U calculations find Weyl state!





They also pointed out very unusual surface states

#### Fermi Arcs

 On most surfaces, metallic Fermi surfaces which are not closed - "arcs" - terminate at the projections of the Weyl points





24 Weyl points predicted in Y<sub>2</sub>Ir<sub>2</sub>O<sub>7</sub>

#### Heterostructuring



• A: yes! And you can do it with topological insulators



#### TI to NI transition





strong tunneling across the NI "heals" TI Tunneling across TI slabs kills the 3d TI

#### TI to NI transition



in between is a (quantum) phase transition

NI

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### TI to NI transition



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strong tunneling across the NI ''heals'' TI

We can turn this critical point into the sla Weyl semimetal by breaking() or TR S. Murakami, 2007

Tunneling across TI slabs kills the 3d TI

Dope with magnetic impurities (already achieved in Bi-based TIs)

ТΙ



model just in terms of surface states

Dope with magnetic impurities (already achieved in Bi-based TIs)



Dope with magnetic impurities (already achieved in Bi-based TIs)



TI  $\epsilon_{k\pm}^2 = v_F^2 k_{\perp}^2 + [m \pm \Delta(k_z)]^2$   $\Delta(k_z) = \sqrt{\Delta_s^2 + \Delta_d^2 + 2\Delta_s \Delta_d \cos(k_z d)}$ 

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$$\mathbf{k}_{\mathbf{z}} \qquad \mathbf{k}_{\mathbf{z}} \qquad \mathbf{k}_{\mu}(k) = \frac{1}{8\pi} \epsilon_{\mu\nu\lambda} \hat{\mathbf{d}} \cdot \partial_{\nu} \hat{\mathbf{d}} \times \partial_{\lambda} \hat{\mathbf{d}} + \mathbf{k}_{\mu\nu\lambda} \hat{\mathbf{d}} \cdot \partial_{\mu} \hat{\mathbf{d}} \times \partial_{\lambda} \hat{\mathbf{d}} + \mathbf{k}_{\mu\nu\lambda} \hat{\mathbf{d}} \cdot \partial_{\mu} \hat{\mathbf{d}} \times \partial_{\mu} \hat{\mathbf{d}}$$

m = exchange energy

"monopoles" of Berry curvature

#### Quantum Hall effect

c.f. Haldane 1988



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QAHE in finite multilayer

m = exchange energy

• Asymmetric heterostructure, or intrinsic I breaking



electrostatic potential asymmetry

$$\epsilon_{k\pm}^2 = v_F^2 (|k_{\perp}| \pm V)^2 + |\Delta(k_z)|^2$$

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electrostatic potential asymmetry

$$\epsilon_{k\pm}^2 = v_F^2 (|k_{\perp}| \pm V)^2 + |\Delta(k_z)|^2$$

Naively gives nodal ring at critical point with  $\Delta_s = \Delta_d$ 

• Asymmetric heterostructure, or intrinsic I breaking



electrostatic potential asymmetry

$$\epsilon_{k\pm}^2 = v_F^2 (|k_{\perp}| \pm V)^2 + |\Delta(k_z)|^2$$

Need to include k-dependence of  $\Delta_s, \Delta_d$ 

Asymmetric heterostructure, or intrinsic I breaking





m = exchange energy

• Asymmetric heterostructure, or intrinsic I breaking





# Hg<sub>I-x</sub>Cd<sub>x</sub>Te structures

- Checked this with semirealistic 10-orbital tight binding model for (Hg,Cd)Te superlattices with asymmetry
- Advantage: can be grown with very high quality
- Disadvantage: strain must be controlled



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# Graphene-like Physics

 2d graphene physics can already be achieved in HgTe quantum wells



Peak width and mobilities comparable with/better than free standing graphene Scattering mechanisms: probably mass fluctuations + Coulomb (fit is Kubo model)

L. Molenkamp: HgTe QWs are "better graphene"

# "3d graphene"

- The transport behavior of 3d Dirac/Weyl fermions is subtle and interesting!
- Naive argument (no disorder or interactions):

 $\operatorname{Re} \sigma(\omega, T=0) \propto \omega$ 

• insulating?

# With impurities

- Usually impurities induce elastic scattering that dominates at low T
  - Here, Born approximation is valid (disorder is *irrelevant* in RG sense)



• Contrast graphene: higher order corrections induce non-zero scattering rate at zero frequency (SCBA)  $1/\tau \sim e^{-\frac{c}{u_{imp}}}$ 

## With impurities

 Neutral impurities w/o interactions leads to non-zero DC conductivity

 $\operatorname{Re}\sigma(\omega,T)\propto\sigma_0f(\omega/T^2)$ 



#### With interactions

- Coulomb interactions are marginal characterized by dimensionless fine structure constant  $\alpha = e^2/\epsilon v_F$ 
  - Leads to strong scattering  $1/\tau \sim \alpha^2 \max(\omega, T) \gg u_{imp} \omega^2$
  - Then expect

$$\sigma_{\rm dc} \sim e^2 \left(\frac{\epsilon^2}{v_F^3}\right) v_F^2 \tau \sim \frac{k_B T}{\alpha}$$
 power law insulator

### Experiment?

 Experiments on Eu<sub>2</sub>Ir<sub>2</sub>O<sub>7</sub> find "weak" insulator



#### Tafti et al, 2011 and private communications

#### Donors

- This is likely related to combined effect of small carrier density and Coulomb scattering from donors - O vacancies
- Follow ideas of calculation for graphene but for 3d

c.f. Nomura+MacDonald, 2007

#### Donors

• Screening

$$V(q) \sim \frac{e^2}{q^2 + \xi^{-2}} \qquad \qquad \xi^{-2} \sim \alpha k_F^2$$

• Scattering

$$\tau^{-1} \sim n \int d^3 q \,\delta(\epsilon_q - \epsilon_F) |V(k+q)|^2 v(k \cdot q)$$
$$\sim e^2 k_F \alpha \int d\cos\theta \frac{1 - \cos^2\theta}{[2(1 + \cos\theta) + \alpha]^2}$$

c.f. Nomura+MacDonald, 2007

#### Donors

#### • Conductivity

$$\sigma \sim e^2 \left(\frac{k_F^2}{v_F}\right) v_F^2 \tau$$
$$\sim f(\alpha) e^2 n^{1/3} \qquad f(\alpha) \sim 1 + \frac{1}{\alpha^2 \ln \alpha}$$

#### • Mean free path

$$\sigma \sim e^2 k_F \cdot k_F \ell \qquad \qquad k_F \ell \sim f(\alpha)$$



## Conclusions



- Weyl semimetals occur in the same sorts of materials as topological insulators (and others!), if *inversion* or *time reversal* are broken
- They can be designed as intermediate states between certain TIs and NIs
- They have unique transport properties and surface states, and in some respects are 3d analogs of graphene, with interactions and defects playing crucial roles